NX2301P 20 V, 2 A P-channel Trench MOSFET Rev. 1 – 26 October 2010

**Product data sheet** 

### 1. Product profile

### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### **1.2 Features and benefits**

- 1.8 V R<sub>DSon</sub> rated for Low Voltage Gate Drive
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

### **1.3 Applications**

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C	-	-	-20	V
$V_{GS}$	gate-source voltage	T <sub>amb</sub> = 25 °C	-	-	±8	V
I <sub>D</sub>	drain current	$T_{amb}$ = 25 °C; V <sub>GS</sub> = -4.5 V	<u>[1]</u> _	-	-2	А
R <sub>DSon</sub>	drain-source on-state resistance	$T_j = 25 °C;$ $V_{GS} = -4.5 V;$ $I_D = -1 A$	[2] _	100	120	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>, t  $\leq$  5 s.



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### 2. Pinning information

Table 2.	Pinning			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		2
2	S	source		
3	D	drain		G
				017aaa094

### 3. Ordering information

Table 3. Ord	Table 3.       Ordering information			
Type number	Package			
	Name	Description	Version	
NX2301P	TO-236AB	plastic surface-mounted package; 3 leads	SOT23	

### 4. Marking

Table 4. Marking codes	
Type number	Marking code <sup>[1]</sup>
NX2301P	MG*

[1] \* = placeholder for manufacturing site code

### 5. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

			-			
Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{\text{DS}}$	drain-source voltage	$T_{amb} = 25 \ ^{\circ}C$	-	-20	V	
$V_{GS}$	gate-source voltage	$T_{amb} = 25 \ ^{\circ}C$	-	±8	V	
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V	[1]			
		T <sub>amb</sub> = 25 °C	-	-2	А	
		$T_{amb} = 100 \ ^{\circ}C$	-	-1.2	А	
I <sub>DM</sub>	peak drain current	$T_{amb} = 25 \text{ °C};$ single pulse; $t_p \le 10 \mu\text{s}$	-	-6	A	

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In accordance with the Absolute Maximum Rating System (IEC 60134).					
Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub> total power dissipation	T <sub>amb</sub> = 25 °C	[2] _	400	mW	
			<u>[1]</u> _	710	mW
		T <sub>sp</sub> = 25 °C	-	2.8	W
Tj	junction temperature			150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C
Source-d	rain diode				
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u> _	-0.7	А

Limiting values ... continued Table 5.

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>, t  $\leq$  5 s.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	<u>[1]</u> _	-	315	K/W
	junction to ambient		[2] _	-	175	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	45	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>, t  $\leq$  5 s.



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## 7. Characteristics

<b>Table 7.</b> $T_j = 25 \ ^{\circ}C \ \iota$	Characteristics unless otherwise specified.						
Symbol	Parameter	Conditions	М	in	Тур	Max	Unit
Static char	racteristics						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_{D} = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V$	-2	20	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = -250 \ \mu\text{A}; \ V_{DS} = V_{GS}$	-(	0.5	-0.75	-1.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V};  V_{GS} = 0 \text{ V}$	-		-	-1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = ±8 V; $V_{DS}$ = 0 V	-		-	±100	nA
$R_{DSon}$	drain-source on-state		<u>[1]</u>				
	resistance	$V_{GS}$ = -4.5 V; $I_{D}$ = -1 A					
		T <sub>j</sub> = 25 °C			100	120	mΩ
		T <sub>j</sub> = 150 °C			-	180	mΩ
		$V_{GS}$ = –2.5 V; $I_{D}$ = –1 A	-		155	190	mΩ
	$V_{GS} = -1.8 \text{ V};$ $I_D = -0.2 \text{ A}$	-		210	270	mΩ	
<b>g</b> <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; \text{ I}_{D} = -2 \text{ A}$	<u>[1]</u> _		4.7	-	S
Dynamic o	haracteristics						
Q <sub>G(tot)</sub>	total gate charge	$I_D = -2.2 \text{ A}; V_{DS} = -6 \text{ V};$	-		4.5	6	nC
$Q_{GS}$	gate-source charge	V <sub>GS</sub> = -4.5 V	-		1.1	-	nC
$Q_{GD}$	gate-drain charge		-		0.9	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = -6 V;$	-		380	-	pF
C <sub>oss</sub>	output capacitance	f = 1 MHz	-		135	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-		115	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DD} = -6 V;$	-		7	-	ns
t <sub>r</sub>	rise time	$R_L = 6 \Omega;$	-		15	-	ns
t <sub>d(off)</sub>	turn-off delay time	$R_G = 6 \Omega$	-		50	-	ns
t <sub>f</sub>	fall time		-		25	-	ns
Source-dra	ain diode						
V <sub>SD</sub>	source-drain voltage	$I_S = -1 \text{ A}; V_{GS} = 0 \text{ V}$	<u>[1]</u> -		-0.8	-1.0	V

[1] Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.01.$ 



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## 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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### 9. Package outline



#### Fig 18. Package outline SOT23 (TO-236AB)

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## 10. Soldering



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## 11. Revision history

Table 8. Revision histo	ry			
Document ID	Release date	Data sheet status	Change notice	Supersedes
NX2301P v.1	20101026	Product data sheet	-	-

### 12. Legal information

### 12.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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